# **B.TECH/ECE/8**<sup>TH</sup> **SEM/ECEN 4221/2022**

# LOW POWER HIGH PERFORMANCE DIGITAL VLSI CIRCUIT DESIGN (ECEN 4221)

Time Allotted: 3 hrs Full Marks: 70

Figures out of the right margin indicate full marks.

Candidates are required to answer Group A and anv 5 (five) from Group B to E, taking at least one from each group.

Candidates are required to give answer in their own words as far as practicable.

# Group - A

			(Multiple Choice	ce Type (	Questic	ons)	
1.	Choo	10 × 1 = 10					
	(i)	With Technology advancement via contact (a) increases (c) remains same			(b) ded	ance creases rd to say.	
	(ii)	Average wide delay is changing with Tecl (a) increasing (c) remaining same			nnology advancement in following way (b) decreasing (d) increasing and then decreasing.		
	(iii)	In Die Variation (IDV) means variation (a) lot to lot (c) within wafer			<ul><li>(b) inside die</li><li>(d) wafer to wafer.</li></ul>		
	(iv)	If channel length of driver transistor is (a) decreases 2x (c) decreases 4x		istor is inc	ncreased 2x, delay of digital gate (b) increases 2x (d) remains same.		
	(v)	If P <sub>A</sub> is signal output is (a) P <sub>A</sub>	probability of a input $(b)$ 1- $P_A$	put of inv (c)		ne signal proba	bility of inverte
	(vi)	From 65 nm onwards below power is ma (a) dynamic (c) short circuit			aximum in a chip (b) leakage (d) contention.		
	(vii)	The critical path for a design refers to (a) the path having maximum delay (c) the path with optimum delay			<ul><li>(b) the path with minimum delay</li><li>(d) the path with no delay.</li></ul>		
	(viii)	Activity Factor is maximum for below circ (a) memory node (c) static			ruit outp (b) dyr (d) clo	namic	

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6. (a) For 3 input NAND gate, mention leaking transistors (channel leakage) for all possible combination of inputs. [(CO6)(Evaluate/HOCQ)]

(b) Explain how both channel and gate leakage can be reduced in FINFET transistor without compromising delay performance with respect to traditional transistor? [(CO6)(Analyze/IOCQ)]

6 + 6 = 12

7. (a) Sketch the Y chart for simplified VLSI design flow in three domains.

[(CO1)(Remember/LOCQ)]

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(b) Explain difference between pre-layout and post layout timing verifications.

[(CO1)(Analyze/IOCQ)]

6 + 6 = 12

# Group - E

- 8. (a) Briefly explain interconnect capacitance components. [(CO3)(Analyze/IOCQ)]
  - (b) Why driver side of a wire needs to be low resistance and receiver side of the wire needs to be low capacitance, explain using Elmore Delay model.

[(CO3)(Analyze/IOCQ)]

6 + 6 = 12

9. (a) Write flow chart of VLSI Design and Verification Cycle.

[(CO1)(Remember/LOCQ)]

(b) What is parasitic Extraction and Back Annotation?

[(CO1)(Understand/LOCQ)]

6 + 6 = 12

Cognition Level	LOCQ	IOCQ	HOCQ
Percentage distribution	37.5	37.5	25

## **Course Outcome (CO):**

After the completion of the course students will be able to

- 1. Learn timing Verification flows
- 2. Learn Static Timing Analysis Method
- 3. Learn Interconnect Design
- 4. Learn Process Variation impact on design
- 5. Learn Dynamic Power Reduction Techniques
- 6. Learn Standby Power Reduction Techniques

\*LOCQ: Lower Order Cognitive Question; IOCQ: Intermediate Order Cognitive Question; HOCQ: Higher Order Cognitive Question